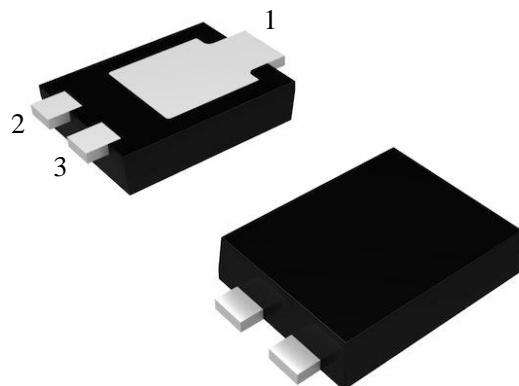
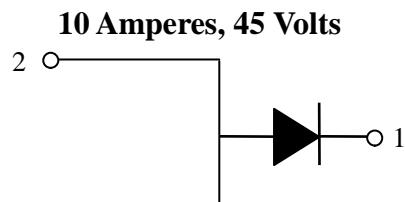


45V Trench MOS Barrier Schottky Low VF 0.45V@10A, 25 °C

Features

- Trench MOS schottky technology
- Low stored charge Majority Carrier Conduction
- Ultra low forward voltage drop
- Low leakage current
- Low power loss and high efficiency
- High surge capacity
- ESD rating:>20K volts



Typical Application

Schottky rectifier design for high frequency switched mode power supplies, such as adaptors and on board DC/DC converters.

TO-277

Device Summary

| Symbol | Value |
|--------------------------|--------|
| I _F (AV) | 10A |
| V _{RRM} | 45V |
| V _F (Typical) | 0.45V |
| T _j (max) | 150 °C |

Mechanical Data

Case: JEDEC TO-277 molded plastic body

Terminals: Plated leads, solderable per MIL-STD-750, Method 2026

Mounting Position: Any

Note: Pins 2 & 3 must be electrically connected at the printed circuit board.

| Major Rating and Characteristics | | | | | |
|----------------------------------|---|--------------------------------|--------------------------|------------|-------|
| Symbol | Parameter | | | Values | Units |
| V_{RRM} | Repetitive peak reverse voltage | | | 45 | V |
| T_J | Storage temperature range | | | -55 to 150 | °C |
| $I_{F(SM)}$ | Surge non repetitive forward current | 10 ms sine or 6 ms rect. pulse | | 150 | A |
| $I_{F(AV)}$ | Maximum average forward current 50 % duty cycle, rectangular waveform | | $T_c=35^{\circ}\text{C}$ | 10 | |

| Electrical Characteristics($T_A=25^{\circ}\text{C}$ unless otherwise noted) | | | | | | |
|--|--|---------------------------|------|------|-------|--|
| Parameter | Test condition | Symbol | TYP | MAX | UNITS | |
| Forward Voltage drop | $I_F=5\text{A}$ | $T_A=25^{\circ}\text{C}$ | 0.39 | - | V | |
| | $I_F=7.5\text{A}$ | | 0.42 | | | |
| | $I_F=10\text{A}$ | | 0.45 | 0.5 | | |
| | $I_F=5\text{A}$ | $T_A=125^{\circ}\text{C}$ | 0.3 | - | | |
| | $I_F=7.5\text{A}$ | | 0.35 | | | |
| | $I_F=10\text{A}$ | | 0.39 | 0.45 | | |
| Reverse leakage current | $V_R=45\text{V}$ | $T_A=25^{\circ}\text{C}$ | 30 | 100 | uA | |
| | | $T_A=125^{\circ}\text{C}$ | 18 | 70 | mA | |
| Junction capacitance | $V_R=5\text{V}_{\text{DC}}, 25^{\circ}\text{C}(1\text{MHz})$ | C_j | - | | pF | |

Notes (1) Pulse test: 300us pulse width,2% duty cycle (2) Pulse test: 300us pulse width,2% duty cycle

| Thermal Characteristics($T_A=25^{\circ}\text{C}$ unless otherwise noted) | | | | |
|---|----------------|-----------|--|-------|
| Parameter | Symbol | SK10U45MA | | UNIT |
| Typical thermal resistance | $R_{JA}^{(1)}$ | 75 | | °C /W |
| | $R_{JM}^{(2)}$ | 34 | | |

Notes

- (1) Free air, mounted on recommended PCB, 2oz.pad area; thermal resistance R_{JA} -junction to ambient
- (2) Cathode pad dimensions 18.8mm x 14.4mm. Anode pad dimensions 5.6mm x 14.4mm;
RJM-junction to mount

Characteristics Curves($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Fig.1 Typical Forward Voltage Characteristics

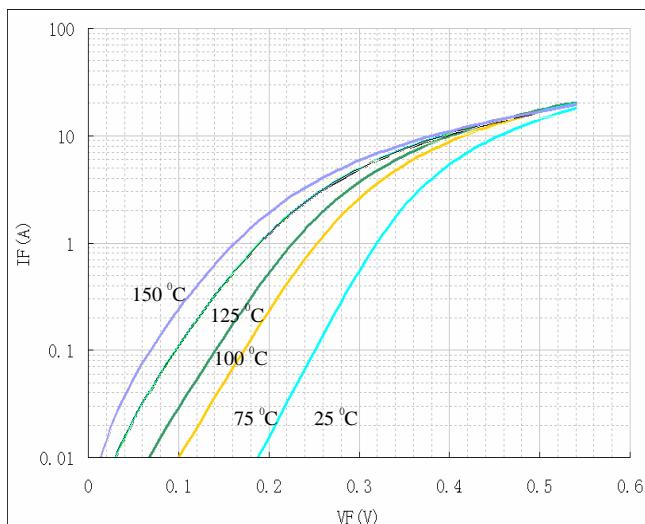
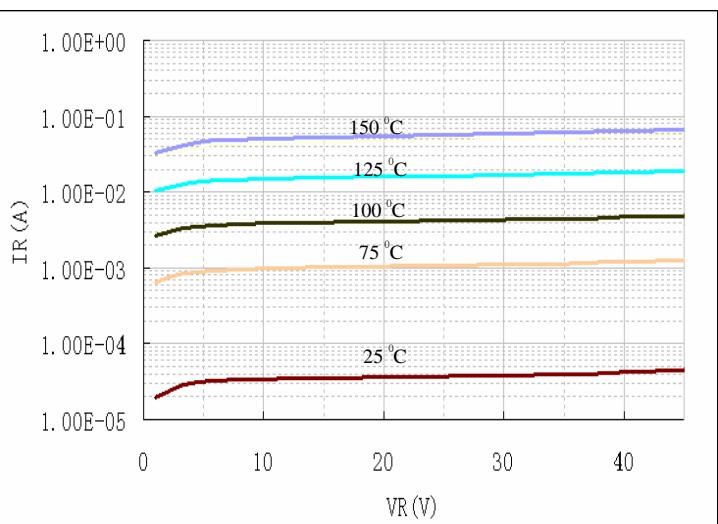


Fig.2 Typical Reverse Leakage Characteristics



Package Outline Dimensions in Millimeters

